



Docket No.: M4065.0319/P319-A
(PATENT)

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John Th

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of:
Ronald A. Weimer, et al.

Application No.: 09/912,558

Group Art Unit: 2813

Filed: July 26, 2001

Examiner: Erik J. Kielin

For: FABRICATION OF DRAM AND OTHER
SEMICONDUCTOR DEVICES WITH AN
INSULATING FILM USING A WET RAPID
THERMAL OXIDATION PROCESS

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AMENDMENT

BOX: Non-Fee Amendment
Commissioner for Patents
Washington, DC 20231

Dear Sir:

This paper is in response to the Office Action dated February 24, 2003 rejecting claims 13, 14, 16, 17, and 41-43, please amend the above-captioned U.S. Patent application as follows:

In the Claims:

Please rewrite claims 13 and 41-43 as follows:

13. (Four Times Amended) A method of fabricating a semiconductor device,
the method comprising:

depositing a dielectric film over an active region of a semiconductor substrate to
form part of a gate of a transistor; and

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